1 Characteristics

Paramete	Value	Unit		
Repetitive peak reverse voltage			60	V
Forward rms current	30	А		
Average forward current	$\begin{array}{c} T_{C} = 140 \ ^{\circ}C \\ \delta = 0.5 \end{array} \begin{array}{c} Per \ diode \\ Per \ device \end{array}$		10 20	A
Surge non repetitive forward current	t _p = 10 ms S	ns Sinusoidal 220		А
Repetitive peak reverse current	t _p = 2 μs squ	are F=1 kHz	1	А
Repetitive peak avalanche power	epetitive peak avalanche power $t_p = 1 \ \mu s \ T_j = 25 \ ^{\circ}C$			W
Storage temperature range	-65 to + 175	°C		
Maximum operating junction tempera	150	°C		
Critical rate of rise reverse voltage	10000	V/µs		
	Repetitive peak reverse voltage Forward rms current Average forward current Surge non repetitive forward current Repetitive peak reverse current Repetitive peak avalanche power Storage temperature range Maximum operating junction tempera	Forward rms currentAverage forward current $T_C = 140 \ ^{\circ}C$ $\delta = 0.5$ Surge non repetitive forward current $t_p = 10 \ ^{\circ}Ms$ Repetitive peak reverse current $t_p = 2 \ \mu s \ ^{\circ}quere squareRepetitive peak avalanche powert_p = 1 \ ^{\circ}MsStorage temperature rangeMaximum operating junction temperature(1)$	Repetitive peak reverse voltageForward rms current $T_C = 140 \ ^{\circ}C$ $\delta = 0.5$ Per diode Per deviceAverage forward current $T_p = 140 \ ^{\circ}C$ Per devicePer diode Per deviceSurge non repetitive forward current $t_p = 10 \ ^{\circ}Ms$ SinusoidalRepetitive peak reverse current $t_p = 2 \ ^{\circ}\mu s \ ^{\circ}Surge results = 1 \ ^{\circ}KT_j = 25 \ ^{\circ}C$ Storage temperature rangeMaximum operating junction temperature ⁽¹⁾	Repetitive peak reverse voltage60Forward rms current60Forward rms current $T_{C} = 140 ^{\circ}C$ $\delta = 0.5$ Per diode Per device10 20Average forward current $T_{p} = 140 ^{\circ}C$ $\delta = 0.5$ Per diode Per device10 20Surge non repetitive forward current $t_{p} = 10 ^{o}ms$ Sinusoidal220Repetitive peak reverse current $t_{p} = 2 ^{\mu}s$ squareF=1 kHz1Repetitive peak avalanche power $t_{p} = 1 ^{\mu}s ^{T} T_{j} = 25 ^{\circ}C$ 5800Storage temperature range-65 to + 175-65 to + 175Maximum operating junction temperature ⁽¹⁾ 150

Table 2. Absolute ratings (limiting values, per diode)

1. $\frac{dPtot}{dT_j} < \frac{1}{Rth(j-a)}$ thermal runaway condition for a diode on its own heatsink

Table 3. Thermal resistances

Symbol	Parameter	Value	Unit	
R _{th (j-c)}	Junction to case	Per diode Total	1.6 0.85	° C/W
R _{th (c)}	Coupling		0.1	° C/W

When the diodes 1 and 2 are used simultaneously:

 ΔT_j (diode 1) = P(diode1) x R_{th(j-c)}(Per diode) + P(diode2) x R_{th(c)}

Table 4. Static electrical characteristics (per diode)

Symbol	Parameter	Tests conditions		Min.	Тур.	Max.	Unit
I _R ⁽¹⁾ Reverse leakage current	Poveres loskers surrent	T _j = 25 °C	V - V			350	μΑ
	T _j = 125 °C	$V_{R} = V_{RRM}$		65	95	mA	
	$V_{\rm F}^{(1)}$ Forward voltage drop	T _j = 25 °C	I _F = 10 A			0.6	
v (1)		T _j = 125 °C	I _F = 10 A		0.48	0.56	V
VF		T _j = 25 °C	I _F = 20A			0.74	v
		T _j = 125 °C	I _F = 20A		0.62	0.7	

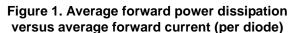
1. Pulse test: t_p = 380 µs, δ < 2%

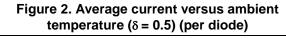
To evaluate the conduction losses use the following equation:

 $P = 0.42 \text{ x } I_{F(AV)} + 0.014 \text{ x } {I_F}^2_{(RMS)}$



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Rth(j-a)=15°C/W

Rth(i-a)=Rth(i-c)

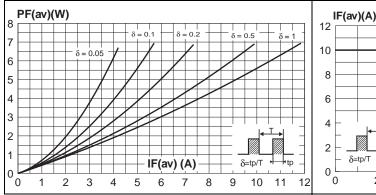
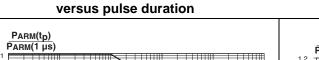
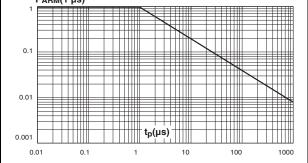


Figure 3. Normalized avalanche power derating Figure 4. Normalized avalanche power derating

25

50





igure 4. Normalized avalanche power derating versus junction temperature

Tamb(°C)

75

100

125

150

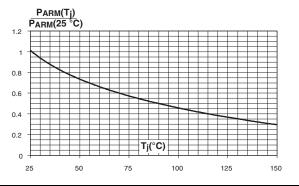


Figure 5. Non repetitive surge peak forward current versus overload duration (maximum values, per diode)

Figure 6. Relative variation of thermal transient impedance junction to case versus pulse duration

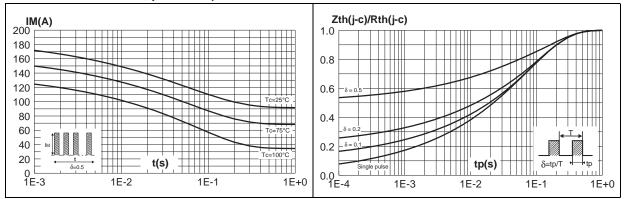




Figure 7. Reverse leakage current versus reverse voltage applied (typical values, per diode)

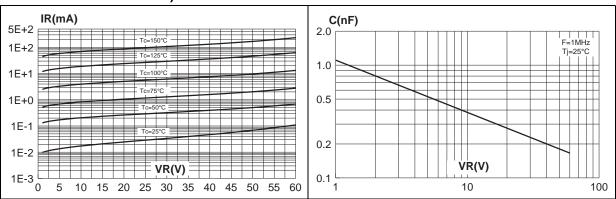
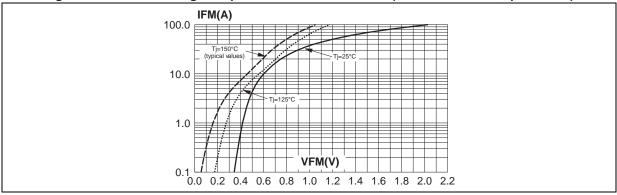


Figure 8. Junction capacitance versus reverse voltage applied (typical values, per diode)

Figure 9. Forward voltage drop versus forward current (maximum values, per diode)





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2 Package information

- Epoxy meets UL94,V0
- Cooling method: conduction
- Recommended torque value: 0.4 to 0.6 N·m

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: *www.st.com.* ECOPACK[®] is an ST trademark.

				Dimer	nsions		
	Ref.	м	illimete	rs		Inches	
		Min.	Тур.	Max.	Min.	Тур.	Max.
	А	4.40		4.60	0.17		0.18
	b	0.61		0.88	0.024		0.034
هPA	b1	0.95		1.20	0.037		0.047
	с	0.48		0.70	0.019		0.027
	D	15.25		15.75	0.60		0.62
	D1		1.27			0.05	
	Е	10.00		10.40	0.39		0.41
	е	2.40		2.70	0.094		0.106
b1(x3)-	e1	4.95		5.15	0.19		0.20
	F	1.23		1.32	0.048		0.052
	H1	6.20		6.60	0.24		0.26
-= e-b (x3)	J1	2.40		2.72	0.095		0.107
← e1 →	L	13.00		14.00	0.51		0.55
	L1	2.60		2.90	0.102		0.114
	L20		15.40			0.61	
	L30		28.90			1.14	
	ØP	3.75		3.85	0.147		0.151
	Q	2.65		2.95	0.104		0.116



Devices in I²PAK with nickel-plated back frame must NOT be mounted by frame soldering like SMDs. Such devices are intended to be through-hole mounted ONLY and in no circumstances shall ST be held liable for any lack of performance or damage arising out of soldering of nickel-plated back frames.

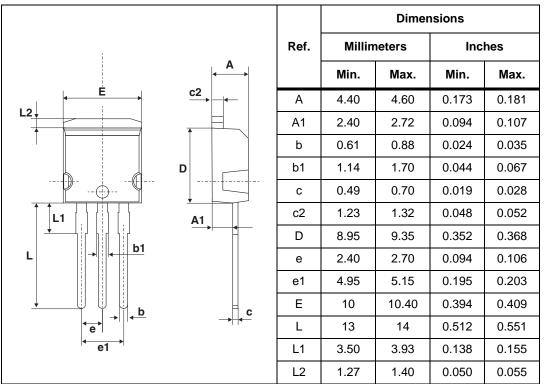


Table 6. I²PAK dimensions



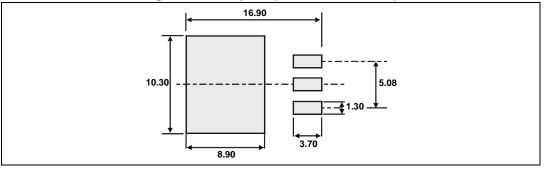
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				Dimensi	ons	
		Ref.	Millimeters		Inches	
			Min.	Max.	Min.	Max.
$\left[- \frac{1}{12} + \frac{1}{12} \right]$		А	4.40	4.60	0.173	0.181
		A1	2.49	2.69	0.098	0.106
		A2	0.03	0.23	0.001	0.009
	В	0.70	0.93	0.027	0.037	
		B2	1.14	1.70	0.045	0.067
		С	0.45	0.60	0.017	0.024
		C2	1.23	1.36	0.048	0.054
		D	8.95	9.35	0.352	0.368
G		E	10.00	10.40	0.393	0.409
		G	4.88	5.28	0.192	0.208
		L	15.00	15.85	0.590	0.624
	M * V2	L2	1.27	1.40	0.050	0.055
	* FLAT ZONE NO LESSTHAN 2mm	L3	1.40	1.75	0.055	0.069
		М	2.40	3.20	0.094	0.126
		R	0.40	typ.	0.01	6 typ.
		V2	0°	8°	0°	8°

Table 7. D²PAK dimensions

Figure 10. Footprint (dimensions in mm)





		Dimensions			
	Ref.	Millin	Millimeters		hes
		Min.	Max.	Min.	Max.
	А	4.40	4.60	0.173	0.181
	С	1.23	1.32	0.048	0.051
H2 A	D	2.40	2.72	0.094	0.107
	E	0.49	0.70	0.019	0.027
	, F	0.61	0.88	0.024	0.034
	F1	1.14	1.70	0.044	0.066
	F2	1.14	1.70	0.044	0.066
	G	4.95	5.15	0.194	0.202
	G1	2.40	2.70	0.094	0.106
F→ ← L4	H2	10	10.40	0.393	0.409
	L2	16.4	16.4 typ.		ō typ.
	L4	13	14	0.511	0.551
	L5	2.65	2.95	0.104	0.116
	L6	15.25	15.75	0.600	0.620
	L7	6.20	6.60	0.244	0.259
	L9	3.50	3.93	0.137	0.154
	М	2.6	typ.	0.102	2 typ.
	Diam.	3.75	3.85	0.147	0.151

Figure 11. TO-220AB dimensions



3 Ordering information

Table 6. Ordering mornation						
Туре	Marking	Package	Weight	Base qty	Delivery mode	
STPS20L60CT	STPS20L60CT	TO-220AB	2.2 g	50	Tube	
STPS20L60CT	STPS20L60CT	TO-220AB	2.2 g	1000	Bulk	
STPS20L60CG	STPS20L60CG	D ² PAK	1.48 g	50	Tube	
STPS20L60CG-TR	STPS20L60CG	D ² PAK	1.48 g	1000	Tape and reel	
STPS20L60CR	STPS20L60CR	I ² PAK	1.49 g	50	Tube	
STPS20L60CTN	STPS20L60CTN	TO-220AB narrow leads	1.9 g	50	Tube	

Table 8. Ordering information

4 Revision history

Table 9. Document revision history

Date	Revision	Changes	
Jul-2003	3C	Previous release	
02-Aug-2013	4	Added TO-220AB narrow leads package.	



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